



8N40

Preliminary

Power MOSFET

**8A, 400V N-CHANNEL
POWER MOSFET**

■ DESCRIPTION

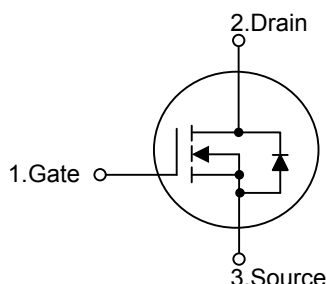
The UTC **8N40** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **8N40** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.

■ FEATURES

- * $R_{DS(ON)}=0.82\Omega @ V_{GS}=10V$
- * High switching speed
- * 100% avalanche tested

■ SYMBOL

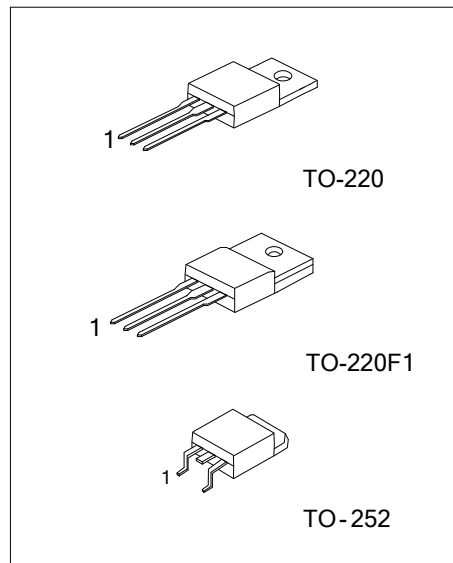


■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N40L-TA3-T	8N40G-TA3-T	TO-220	G	D	S	Tube
8N40L-TF1-T	8N40G-TF1-T	TO-220F1	G	D	S	Tube
8N40L-TN3-T	8N40G-TN3-T	TO-252	G	D	S	Tube
8N40L-TN3-R	8N40G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8N40L-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TN3: TO-252</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_C=25^\circ\text{C}$)	I_D	8	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	320	mJ
	Repetitive (Note 2)	E_{AR}	2.5	mJ
Power Dissipation	TO-220	P_D	104	W
	TO-220F1		39	W
	TO-252		75	W
Derate above 25°C	TO-220		0.832	$\text{W}/^\circ\text{C}$
	TO-220F1		0.312	$\text{W}/^\circ\text{C}$
	TO-252		0.6	$\text{W}/^\circ\text{C}$
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 10\text{mH}$, $I_{AS} = 8\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

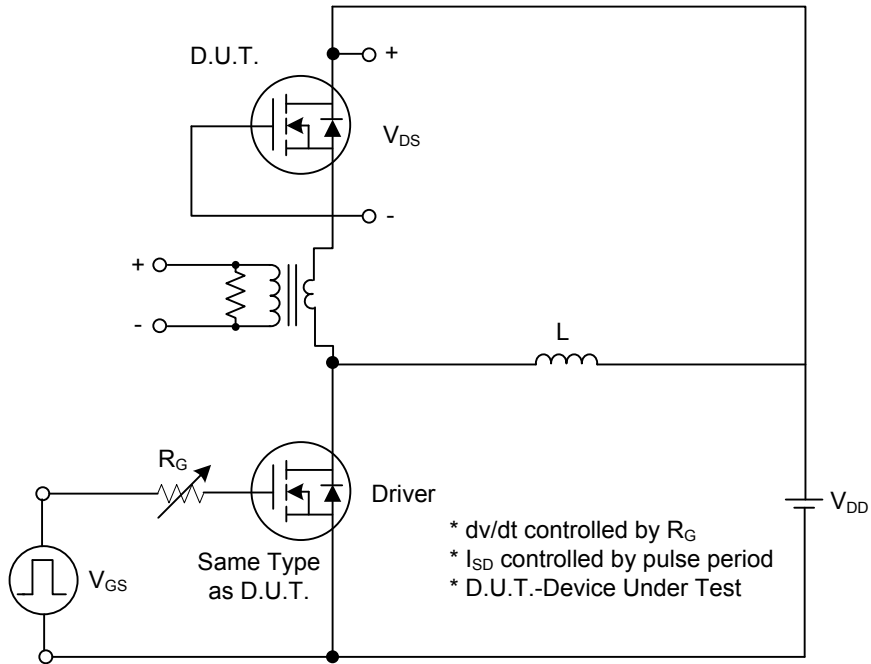
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.2	$^\circ\text{C}/\text{W}$
	TO-220F1		3.18	
	TO-252		2	

■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise specified)

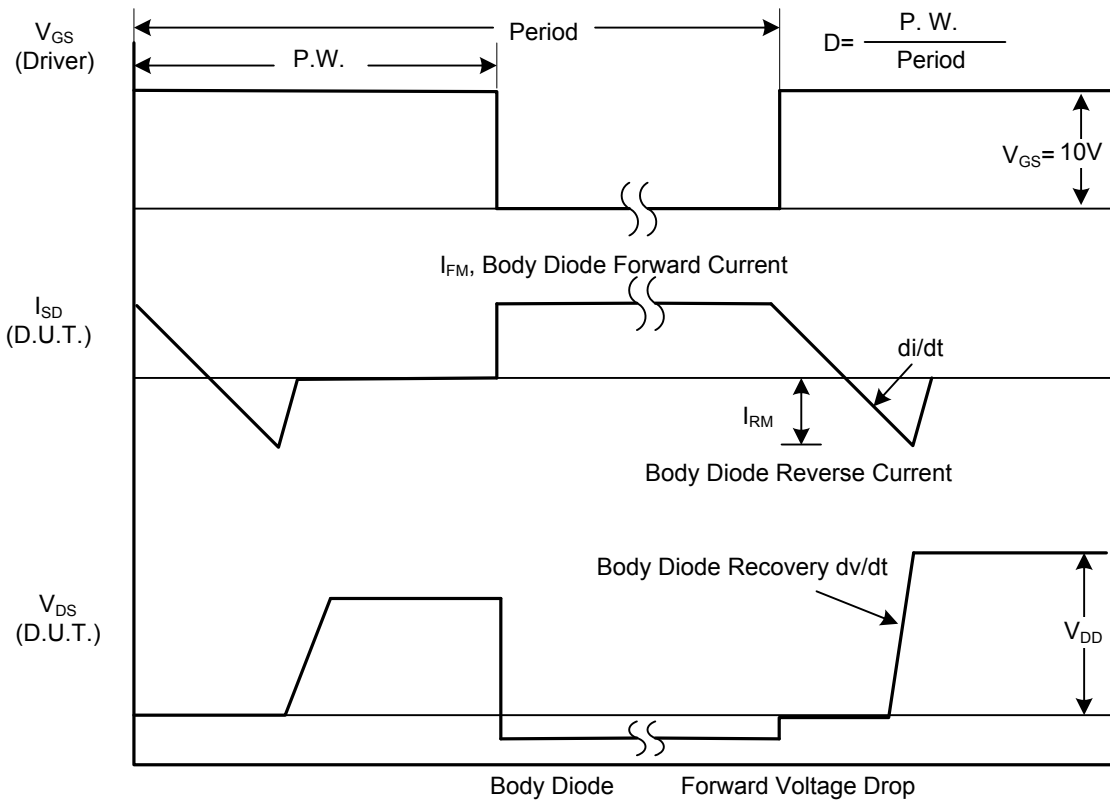
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	400			V
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =250μA		0.4		V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =400V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse	V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4A		0.68	0.82	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz			1600	pF
Output Capacitance	C _{OSS}				450	pF
Reverse Transfer Capacitance	C _{RSS}				150	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{GS} =10V, V _{DS} =320V, I _D =8A (Note 1, 2)		24	60	nC
Gate to Source Charge	Q _{GS}			10		nC
Gate to Drain Charge	Q _{GD}			18		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =200V, I _D =8A, R _G =25Ω (Note 1, 2)		35		ns
Rise Time	t _R			15		ns
Turn-OFF Delay Time	t _{D(OFF)}			90		ns
Fall-Time	t _F			35		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				8	A
Maximum Body-Diode Pulsed Current	I _{SM}				32	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =8A, V _{GS} =0V			1.9	V

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

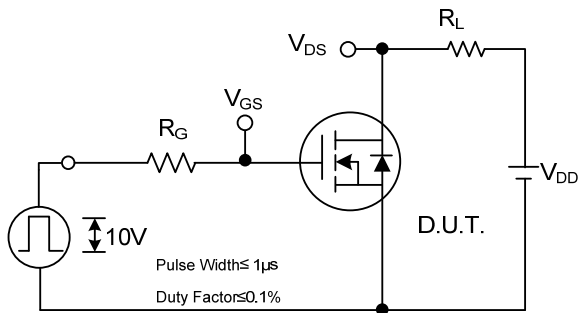


Peak Diode Recovery dv/dt Test Circuit

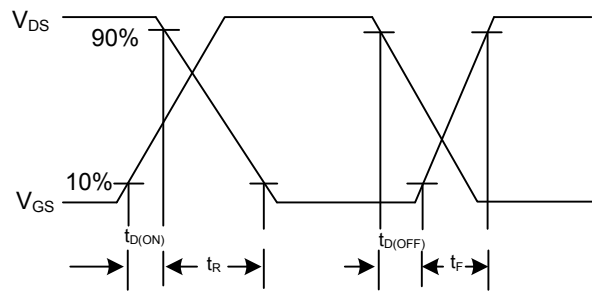


Peak Diode Recovery dv/dt Waveforms

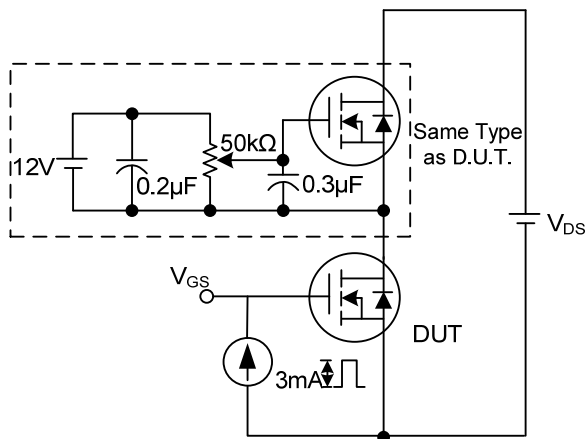
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



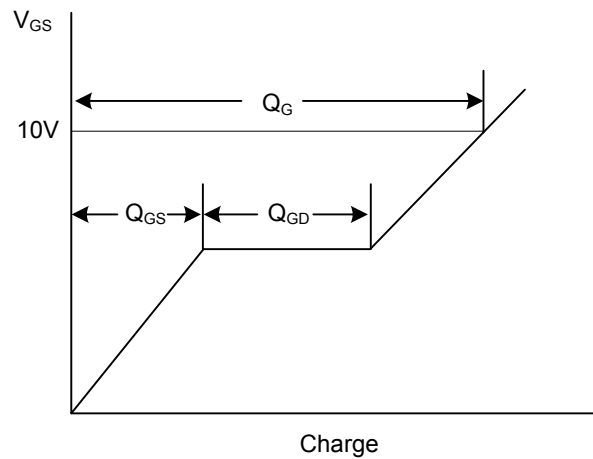
Switching Test Circuit



Switching Waveforms

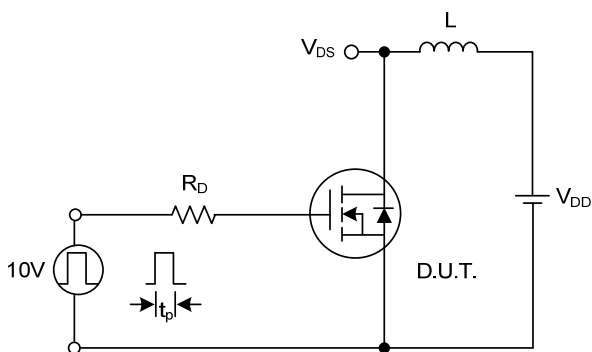


Gate Charge Test Circuit

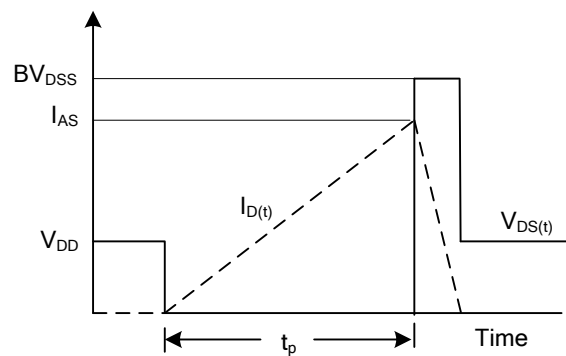


Charge

Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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